



60V N-Channel Enhancement Mode MOSFET

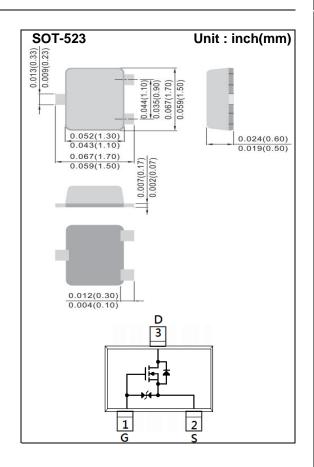
Voltage 60 V Current 160mA

Features

- RDS(ON) , VGS@10V, ID@160mA<4.2Ω
- RDS(ON) , VGS@4.5V, ID@100mA<5Ω
- RDS(ON) , VGS@2.5V, ID@50mA<7Ω
- Advanced Trench Process Technology
- ESD Protected
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std. (Halogen Free)

Mechanical Data

- Case: SOT-523 Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00007 ounces, 0.002 grams
- Marking: E8L



Maximum Ratings and Thermal Characteristics ($T_A=25^{\circ}C$ unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V
Continuous Drain Current		I _D	160	mA
Pulsed Drain Current		I _{DM}	800	mA
Power Dissipation	T _A =25°C	P _D	223	mW
	Derate above 25°C		1.8	mW/°C
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Typical Thermal resistance				
- Junction to Ambient (Note 3)		$R_{\theta JA}$	560	°C/W





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	60	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	0.8	1.2	1.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =160mA	-	2.5	4.2	Ω
		V _{GS} =4.5V,I _D =100mA	-	2.8	5	
		V _{GS} =2.5V,I _D =50mA	-	3.7	7	
		V _{GS} =1.8V,I _D =10mA	-	12	-	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	0.01	1	uA
Gate-Source Leakage Current	I _{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	<u>+</u> 1.0	<u>+</u> 10	uA
Dynamic (Note 4)						
Total Gate Charge	Q_g	V _{DS} =15V, I _D =160mA, V _{GS} =4.5V ^(Note 1,2)	-	0.7	-	nC
Gate-Source Charge	Q_{gs}		-	0.33	-	
Gate-Drain Charge	Q_gd		-	0.2	-	
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V, f=1.0MHZ	-	15	-	pF
Output Capacitance	Coss		-	8.4	-	
Reverse Transfer Capacitance	Crss		-	4.2	-	
Turn-On Delay Time	td _(on)	\\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	-	7	-	
Turn-On Rise Time	tr	$\begin{array}{l} V_{DD}{=}10V,\ I_{D}{=}160mA,\\ V_{GS}{=}10V,\\ R_{G}{=}6\Omega^{(Note\ 1,2)} \end{array}$	-	22	-	ns
Turn-Off Delay Time	td _(off)		-	21	-	
Turn-Off Fall Time	tf		-	25	-	
Drain-Source Diode						
Maximum Continuous Drain-Source	I _S		_	-	160	mA
Diode Forward Current	-3					
Diode Forward Voltage	V_{SD}	I _S =160mA, V _{GS} =0V	-	0.8	1.1	V

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper
- 4. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

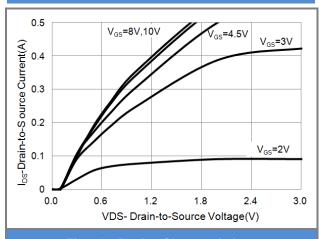


Fig.1 On-Region Characteristics

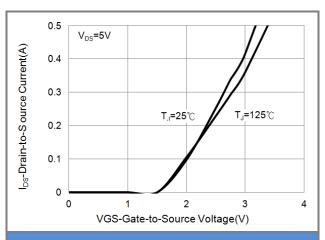


Fig.2 Transfer Characteristics

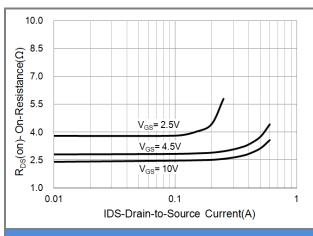


Fig.3 On-Resistance vs. Drain Current

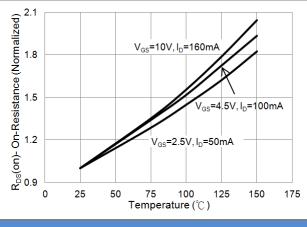


Fig.4 On-Resistance vs. Junction temperature

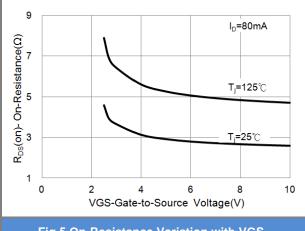


Fig.5 On-Resistance Variation with VGS.

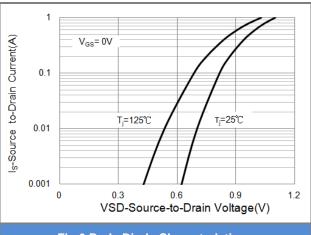


Fig.6 Body Diode Characteristics





TYPICAL CHARACTERISTIC CURVES

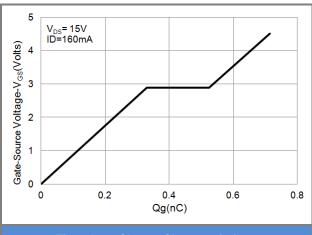
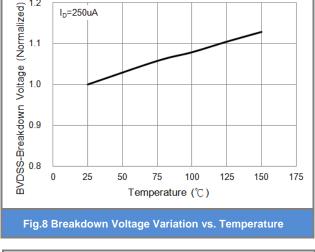


Fig.7 Gate-Charge Characteristics



I_D=250uA

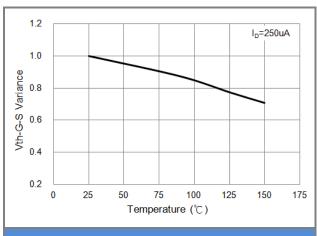


Fig.9 Threshold Voltage Variation with Temperature.

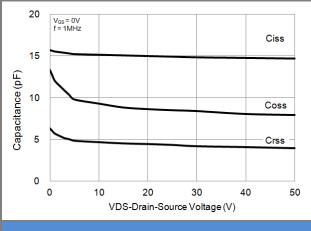


Fig.10 Capacitance vs. Drain-Source Voltage.

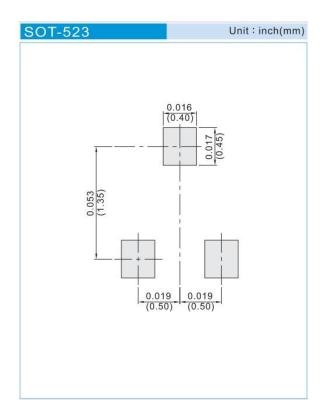




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJE138L_R1_00001	SOT-523	4K pcs / 7" reel	E8L	Halogen free

MOUNTING PAD LAYOUT







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